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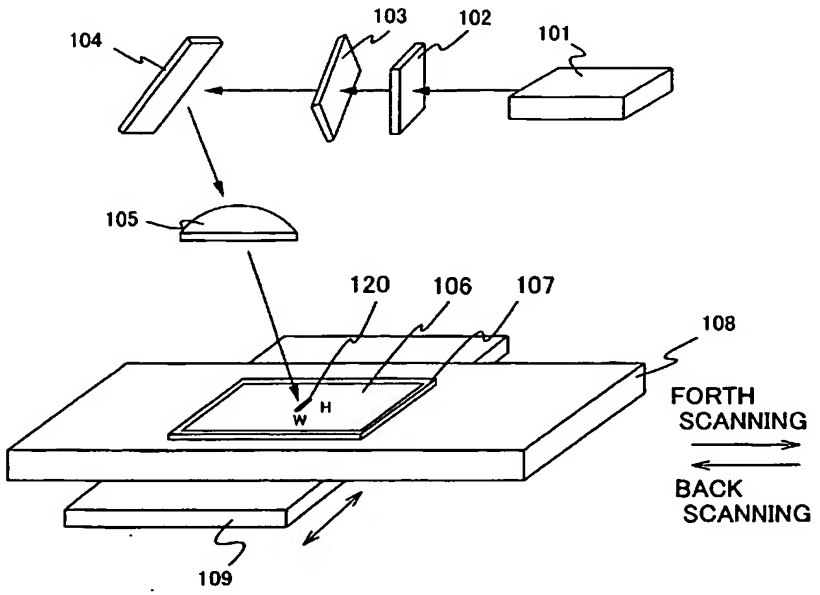
(54) Title: LASER IRRADIATION APPARATUS AND LASER IRRADIATION METHOD



(57) Abstract: It is an object of the present invention to provide a laser irradiation apparatus which can manufacture a homogenously crystallized film by varying the energy intensity of an irradiation beam in forward and backward directions of the irradiation. A laser irradiation apparatus of the present invention comprises a laser oscillator and means for varying beam intensity wherein a laser beam is obliquely incident into the irradiation surface, the laser beam is scanned relative to the irradiation surface, and the beam intensity is varied in accordance with the scanning direction. Further, the laser oscillator is a continuous wave solid-state laser, gas laser, or metal laser. A pulsed laser having a repetition frequency of 10 MHz or more can also be used.

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